

SANYO	No.4650	2SK1908
		N-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance
- Very high-speed switching
- Low-voltage drive
- Surface mount type device making the following possible.
 - Reduction in the number of manufacturing processes for 2SK1908-applied equipment.
 - High-density surface mount applications.
 - Small size of 2SK1908-applied equipment.

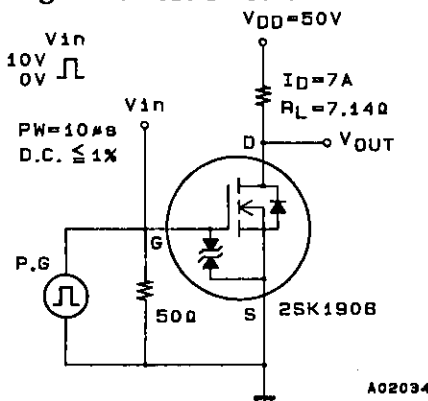
Absolute Maximum Ratings at Ta = 25°C

			unit
Drain-to-Source Voltage	V _{DSS}	100	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Drain Current(DC)	I _D	15	A
Drain Current(Pulse)	I _{DP}	60	A
Allowable Power Dissipation	P _D	1.65	W
		T _c = 25°C	
Channel Temperature	T _{ch}	60	W
Storage Temperature	T _{stg}	150	°C
		-55 to +150 °C	

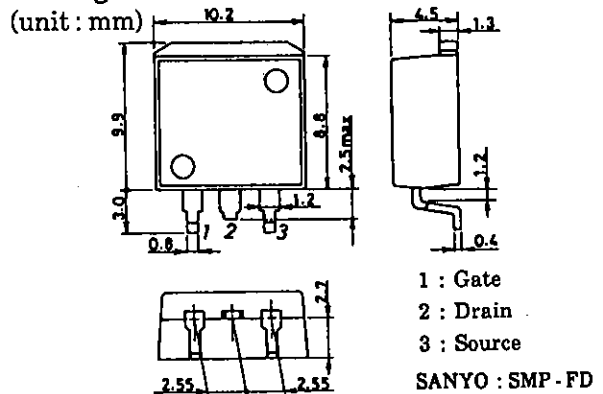
Electrical Characteristics at Ta = 25°C

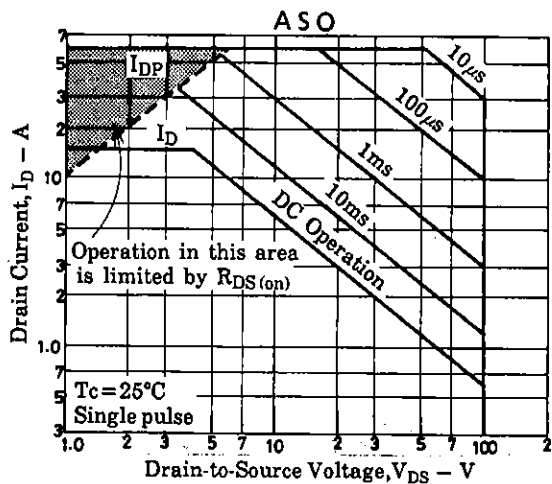
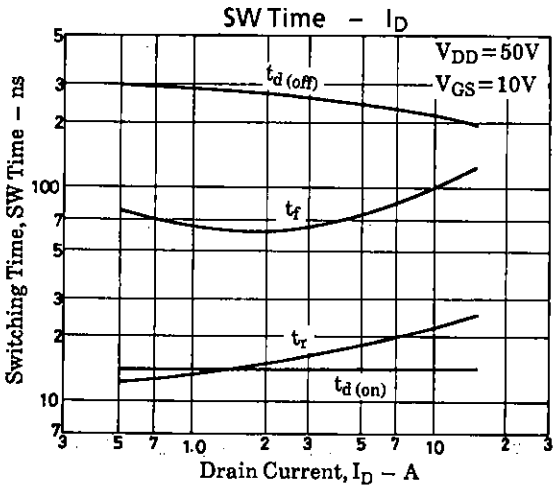
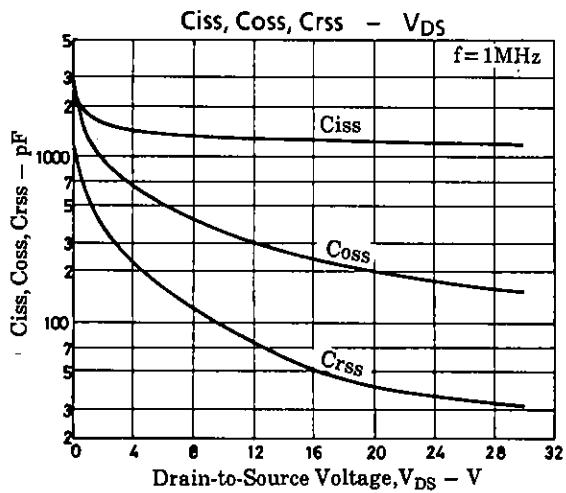
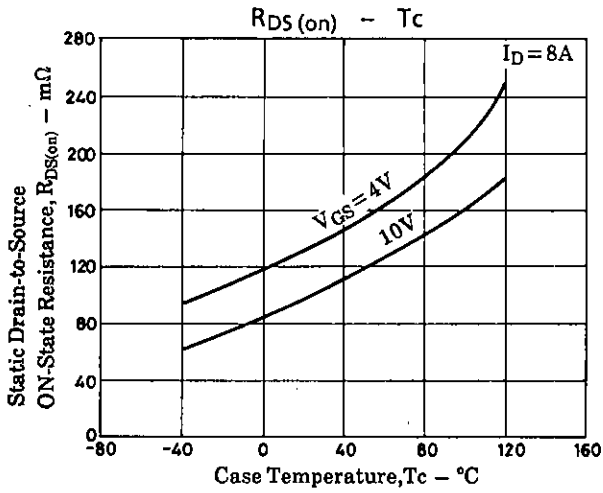
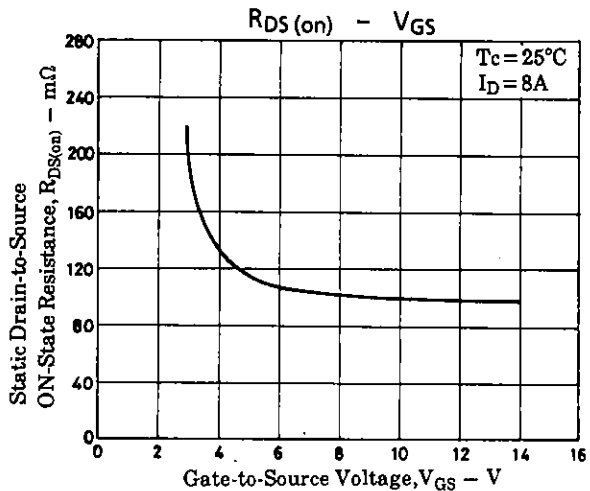
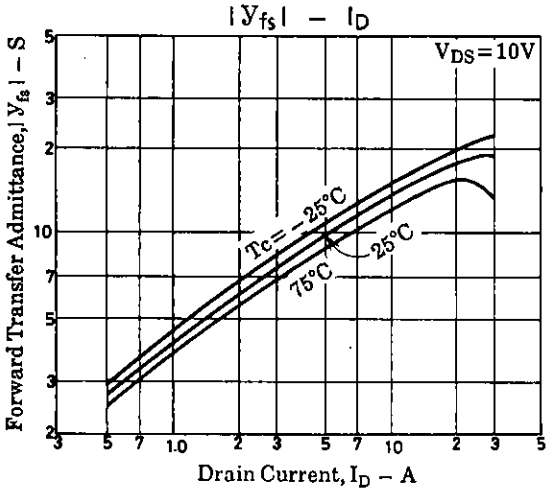
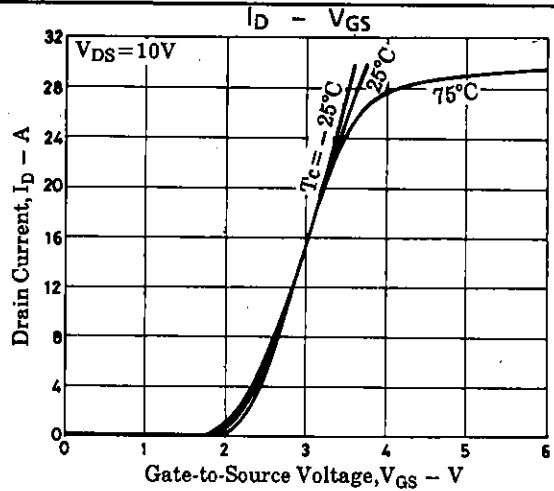
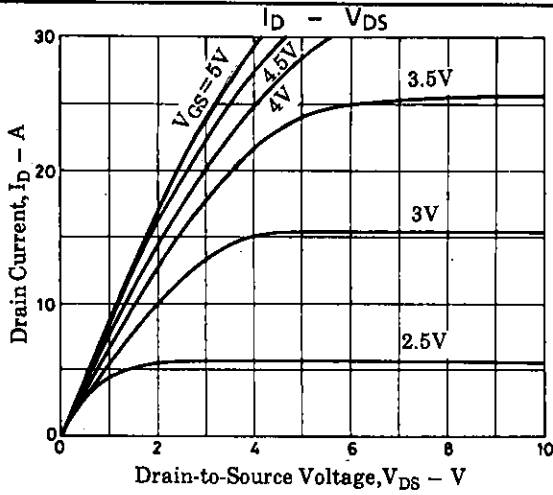
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0	100			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ±100μA, V _{DS} = 0	±20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0			100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±16V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1mA	1.0		2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10V, I _D = 7A	7	11.5		S
Static Drain-to-Source ON-State Resistance	R _{DSON}	I _D = 7A, V _{GS} = 10V		100	135	mΩ
	R _{DSON}	I _D = 7A, V _{GS} = 4V		135	180	mΩ
Input Capacitance	C _{iss}	V _{DS} = 20V, f = 1MHz		1230		pF
Output Capacitance	C _{oss}	V _{DS} = 20V, f = 1MHz		200		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 20V, f = 1MHz		40		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		14		ns
Rise Time	t _r	∞		21		ns
Turn-OFF Delay Time	t _{d(off)}	∞		230		ns
Fall Time	t _f	∞		90		ns
Diode Forward Voltage	V _{SD}	I _S = 15A, V _{GS} = 0	1.0	1.5		V

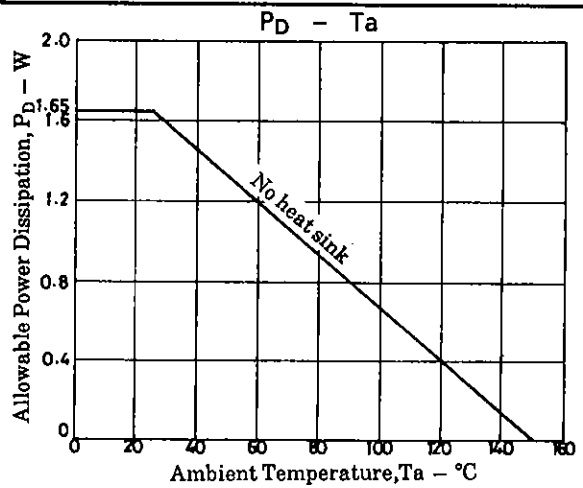
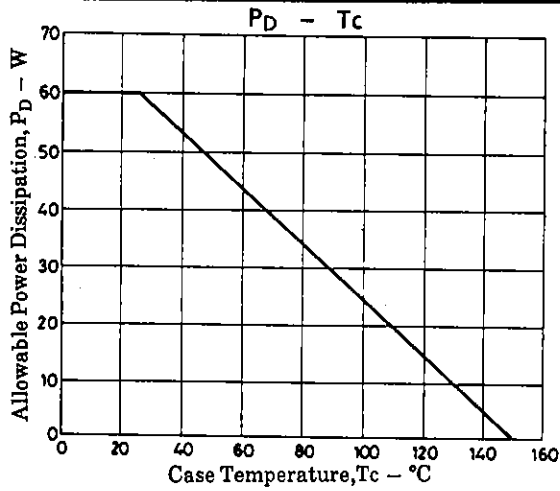
Switching Time Test Circuit



Package Dimensions 2090A







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